

L Number	Hits	Search Text	DB	Time stamp
3	13	(US-6707711-\$ or US-6611405-\$ or US-6555889-\$ or US-6325900-\$ or US-6219212-\$ or US-5650958-\$ or US-6636399-\$ or US-6710984-\$ or US-6624987-\$ or US-6545848-\$ or US-6233172-\$).did. or (US-20010040778-\$ or US-20040095690-\$).did.	USPAT; US-PGPUB	2004/06/22 15:04
4	0	mram and (free or sense or sensing) near10 (spacer or interlayer near insulating or side or sidewall) near4 (sin or nitride)	USPAT; US-PGPUB	2004/06/22 15:05
5	2	mtj and (free or sense or sensing) near10 (spacer or interlayer near insulating or side or sidewall) near4 (sin or nitride)	USPAT; US-PGPUB	2004/06/22 15:06
6	2	mtj and (free or sense or sensing) near10 (spacer or interlayer near insulating or side or sidewall) near4 (sin or nitride)	USPAT; US-PGPUB	2004/06/22 15:06
-	555	(mram or memory) and (free or sense or sensing) with (pinned or fixed) with (length or width)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/21 08:40
-	128	(mram or memory) and (free or sense or sensing) with (pinned or fixed) with ((length or width) near3 (smaller or larger or greater or bigger or less or lesser or more or increased or decreased or different or differing) or wider or longer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 15:02
-	31	(mram or (magnetic or ferromagnetic or magnetoresistive or magnetoresistance or magneto-resistive or magneto-resistance) near2 (memory or storage)) and (free or sense or sensing) with (pinned or fixed) with ((length or width) near3 (smaller or larger or greater or bigger or less or lesser or more or increased or decreased or different or differing) or wider or longer) and (pinning or antiferromagnetic or anti-ferromagnetic or afm)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 15:32
-	2	6485989.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 15:17
-	7	("3553660" "4780848" "4897288" "4918655" "5060193" "5756366" "6211559").PN.	USPAT	2004/06/10 15:18
-	640	(mram or (magnetic or ferromagnetic or magnetoresistive or magnetoresistance or magneto-resistive or magneto-resistance) near2 memory) and (tunnel near2 junction or tunnel near oxide or tunneling near oxide or mtj or tmr) and (free or sense or sensing) and (pinned or fixed) and (pinning or antiferromagnetic or antiferromagnet or afm or anti-ferromagnetic or anti-ferromagnet or fixing)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 14:45
-	56	(mram or (magnetic or ferromagnetic or magnetoresistive or magnetoresistance or magneto-resistive or magneto-resistance) near2 memory) and (tunnel near2 junction or tunnel near oxide or tunneling near oxide or mtj or tmr) and (free or sense or sensing) and (pinned or fixed) and (pinning or antiferromagnetic or antiferromagnet or afm or anti-ferromagnetic or anti-ferromagnet or fixing) and (free or sense or sensing) near5 (patterning or patterned or etched or etching or trimmed or trimming)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 15:01
-	4	("5801984" "5828598" "5898612" "5959880").PN.	USPAT	2004/06/18 14:50

-	45	(mram) and (free or sense or sensing) and (pinned or fixed) and (pinning or antiferromagnetic or antiferromagnet or afm or anti-ferromagnetic or anti-ferromagnet or fixing) and (free or sense or sensing) near5 (patterning or patterned or etched or etching or trimmed or trimming)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 15:37
-	191	(mram or fram) and (free or sense or sensing) and (pinned or fixed) and (pinning or antiferromagnetic or antiferromagnet or afm or anti-ferromagnetic or anti-ferromagnet or fixing) and (free or sense or sensing) near5 (width or length or smaller or larger or wider or longer or shorter or shape or shaped)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 16:26
-	1	(mram or fram) and (free or sense or sensing) and (pinned or fixed) and (pinning or antiferromagnetic or antiferromagnet or afm or anti-ferromagnetic or anti-ferromagnet or fixing) and (free or sense or sensing) near2 (oxidized or oxidize or oxidation or oxidization or oxidizing or oxide) near2 (side or edge or sidewall)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 16:32
-	5	(mram or fram) and (free or sense or sensing) and (pinned or fixed) and (pinning or antiferromagnetic or antiferromagnet or afm or anti-ferromagnetic or anti-ferromagnet or fixing) and (free or sense or sensing) near6 (oxidized or oxidize or oxidation or oxidization or oxidizing or oxide) near2 (side or edge or sidewall or outer or outside or fringe)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 16:33
-	6	(mram or fram) and (free or sense or sensing) and (pinned or fixed) and (pinning or antiferromagnetic or antiferromagnet or afm or anti-ferromagnetic or anti-ferromagnet or fixing) and (free or sense or sensing) near6 (oxidized or oxidize or oxidation or oxidization or oxidizing or oxide) near4 (side or edge or sidewall or outer or outside or fringe)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 16:33
-	13	(US-6545848-\$ or US-6624987-\$ or US-6233172-\$ or US-6219212-\$ or US-6325900-\$ or US-6611405-\$ or US-6636399-\$ or US-6710984-\$ or US-6707711-\$ or US-6555889-\$ or US-5650958-\$).did. or (US-20040095690-\$ or US-20010040778-\$).did.	USPAT; US-PGPUB	2004/06/18 16:39
-	810	(mram or memory) and (lower or bottom) near3 (electrode or conductor) near4 (trench or groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/21 08:41
-	8	(mram or magnetic near memory) and (lower or bottom) near2 (electrode or conductor) near2 (trench or groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/21 08:45
-	2	(mram or magnetic near memory) and (lower or bottom) near2 (electrode or conductor) near2 (within or recessed or recess or grooved or trenched) near3 (substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/21 08:46